

Index

A

- AC coupling effect
 - frequency responses of, 33
 - impact on BER performance, 36, 39
- Additive White Gaussian noise (AWGN) channel, 28
- Advanced BiCMOS processes
 - at mm-wave frequencies, 127, 195
 - HBT transistors, 127, 186
 - high-speed HBTs, 127
- Agilent 8510XF Network analyzer, 205, 236
- Alternating Current (AC), 203
- AM/AM distortion, 181
- Amplitude Modulation (AM), 183, 191, 216
- AM-PM distortion, 194
- Analog filters
 - external baseband analog filters, 30
 - sampling frequency, 30
 - Wiener filter, 30
 - without Rx equalizer, 30
 - with Rx equalizer, 30
- Analog Intermediate Frequency (AIF), 26, 27
- Analog-to-Digital Converter (ADC), 20, 27, 30, 92, 94, 101
- Automatic Cruise Control (ACC), 5
- Automatic Gain Control (AGC) loops, 197
- Automatic Level Control (ALC) systems, 214

B

- Back End Of Line (BEOL), 117
- Backhaul networks
 - common public radio interface (CPRI) data, 7

- conventional baseband unit (BBU) structures, 7
- remote radio head (RRH), 7
- Bandpass Filter (BPF), 64, 92, 100
- Bandwidth of the signal (BW), 30, 81, 82, 85, 92, 94, 96
- Baseband (BB), 135
- Baseband filters effect
 - simulation model for, 30
- Baseband Unit (BBU), 7
- Baseline BER performance, 30
- BiCMOS integrated circuits
 - IF and mmW front-end blocks, 25
- BiCMOS mmW PAs, 186
- BiCMOS 55-nm process, 117, 119
- Bipolar CMOS (BiCMOS), 2, 3, 6, 9, 22, 25, 117, 118, 124, 127, 129, 132, 135, 141, 145, 147, 163, 164, 171, 185, 186, 188, 190, 195, 202, 207, 218, 231, 235, 246, 247
- Bipolar Junction Transistor (BJT), 177, 180
- BISC circuitry for UWB, 92
- BISC I/Q imbalance compensation method, 100
- BISC Pre-dist. tones, 105
- Bit Error Rate (BER), 15, 25
- Block RX-DUP, 27
- Block TX DUP, 25, 27
- Breakdown Voltage (BV), 128, 130, 184, 185, 195, 197
- Breakdown voltage of HBTs, 128
- Built-in-Self-Calibration (BiSC), 90–94, 97, 100, 105, 107, 109, 112
- Built-in-Self-Test (BIST) techniques, 90

C

- Capacitors, [55](#), [117](#), [119](#), [122–124](#), [132](#), [146](#), [155](#), [165](#), [168](#), [202](#), [232](#), [235](#)
- Centralized or Cloud Radio Access Network (C-RAN), [8](#)
- CG versus LO voltage swing
 - different base bias voltages, [168](#)
- Channel distribution, [The](#), [15](#)
- Channel Separation (CS), [16](#), [40](#), [163](#), [245](#)
- Chip layout, [154](#), [203](#), [223](#), [235](#)
- CMOS and BiCMOS mixers, [145](#), [171](#)
- CMOS and BiCMOS up-converters, [145](#), [163](#)
- Common Base (CB) topology, [168](#)
- Common BiSC circuitry
 - for I/Q imbalance estimation, [90](#), [92](#)
- Common Public Radio Interface (CPRI), [7](#)
- Common-Collector (CC) configuration, [217](#)
- Common-Emitter (CE) configuration, [128](#), [168](#), [186](#), [187](#)
- Common-Source (CS), [178](#)
- Complementary metal-oxide-semiconductor (CMOS), [1](#), [3](#), [5](#), [6](#), [117](#), [141](#), [145](#), [163](#), [171](#), [185](#), [194](#), [198](#), [207](#)
- Continuous Wave (CW), [160](#), [215](#), [219](#), [220](#), [223](#), [226–228](#)
- Conversion Gain (CG), [138](#), [167](#), [236](#)
- Coupling capacitor, [222](#)
- C-RAN approach
 - CPRI interconnect backhaul in, [8](#)
- Custom BiCMOS integrated circuits, [22](#)

D

- DAC₁ and DAC₂, [77](#)
- DAC delay imbalance
 - compensation, [81](#), [83](#), [89](#), [94](#), [97](#), [101](#), [107](#)
 - correction of, [98](#), [101](#)
 - estimation of, [94](#), [95](#)
- Data Clock Input (DCI), [77](#)
- Data Clock Output (DCO), [77](#)
- 1-dB compression point, [180](#), [238](#), [245](#)
- DC-decoupling, [122](#)
- DC power consumption, [145](#), [154](#), [155](#), [188](#), [191](#), [192](#), [195](#), [205](#), [227](#), [236](#)
- Delay estimation flowchart, [96](#)
- Design considerations for the detector core, [219](#)
- Design Rule Check (DRC), [123](#), [124](#)
- Detection frequency range, [215](#)
- Device Under Test (DUT), [215](#), [231](#)
- Digital Baseband (DBB), [26](#), [28](#)

- Digital compensation, [69](#)
- Digital pre-distortion, [69](#), [194](#), [214](#)
- Digital Signal Processing (DSP), [19](#), [194](#)
- Digital-to-Analog Converter (DAC), [20](#), [21](#), [61–63](#), [76–81](#), [83–85](#), [143](#), [147](#), [162](#), [198](#)
- Direct Current (DC), [33](#), [37](#), [179](#), [182](#), [242](#)
- Doherty PA, [the](#), [191](#), [192](#)
- Doherty power amplifier, [191](#), [192](#)
- Double-balanced semi-passive mixer topology, [165](#)
- Double Side-Band (DSB), [152](#)
- Drain efficiency, [179](#), [182](#), [183](#)
- DS0 Digital sub-band centered at -500 MHz, [37](#)
- DS1 Digital sub-band centered at -500 MHz, [37](#)
- 4DSP FMC230 board, [22](#), [76](#), [242](#)
- Dynamic range, [216](#), [244](#)

E

- E-band multi-gigabit transmitters, [247](#)
- Effect of the nonlinearity, [40](#)
- Efficiency enhancement techniques, [191](#)
- Electromagnetic (EM) simulator, [119](#)
- Electrostatic Discharge (ESD), [155](#)
- Elimination and restoration (EER) systems, [192](#)
- Envelope Detector (ED), [90](#)
- Envelope elimination and restoration (EER), [192](#), [193](#)
- Error Vector Magnitude (EVM), [109](#), [112](#), [163](#), [245](#)
- European Communications Committee (ECC), [15](#), [236](#)
- European Telecommunications Standards Institute (ETSI), [6](#), [16](#), [18](#), [40](#), [163](#), [245](#), [247](#)
- EVM and MER measurement, [109](#)

F

- Federal Communications Commission (FCC), [6](#)
- FET or bipolar transistors, [141](#)
- Field-effect transistor (FET), [141](#)
- Field-programmable gate array (FPGA), [22](#), [25](#), [76](#), [77](#), [162](#), [214](#), [242](#), [245](#)
- Figures of merit, [127](#), [135](#), [138](#), [177](#), [209](#), [213](#), [214](#), [228](#)
- Finite impulse response (FIR), [96–99](#), [101](#), [105](#)
- First In, First Out (FIFO), [77](#)

- For wideband mm-wave power amplifiers, 185
 - Forward error correction (FEC) codification, 29
 - Fourier transform of a signals, 49
 - FPGA board, 76
 - Frequency response
 - Maximum oscillation frequency (f_{MAX}), 127
 - transition frequency (f_T), 127
 - Frequency selective I/Q imbalance compensation, 20, 58, 81, 89, 94, 97, 244
 - Frequency-division duplex (FDD), 15
 - Frequency-selective (FS), 55
- G**
- Gain and phase imbalance, 27, 45, 46, 48, 50, 52, 53, 64, 68, 74–76, 95, 96, 98, 101, 104, 105, 107, 111, 112, 242
 - 10-Gbps transmission system, 10, 160, 161, 241
 - 5G Cellular Networks, 7
 - General-Purpose Interface Bus (GPIB), 98
 - Gilbert cell, 142, 145, 149, 155, 165
 - GPIB connection, 98
 - Ground-Signal-Ground (GSG), 154, 155, 203, 223, 235
- H**
- HBT transistor, 119, 127, 129, 132, 165, 186
 - Henri Chireix, 192
 - Heterojunction Bipolar Transistors (HBT), 117, 165, 167, 168, 188, 197, 198, 217
 - Hierarchical QAM modulation, 242
 - High Definition (HD), 5
 - High-Definition Multimedia Interface (HDMI), 5
 - High-Electron-Mobility Transistor (HEMT), 2
 - High-ohmic polycrystalline (HIPO) resistors, 117
 - High-performance Xilinx VC707 FPGA, 22, 242
 - 1-Hz resolution bandwidth, 245
- I**
- I/Q gain and phase imbalance
 - digital compensation and mitigation of, 61
 - I/Q imbalance compensation
 - BiSC comp., 107
 - PSA comp., 107
 - I/Q imbalance correction, 68, 69, 89
 - I/Q imbalance estimation, 59, 71, 83, 89, 90, 92, 95, 98–100, 104, 111, 112, 147
 - I/Q imbalance mitigation methods, 97
 - I/Q modulation of the signal, 42
 - I/Q modulator and demodulators, 45
 - I/Q up-conversion, 19
 - IF feedthrough, 139
 - IF LO buffer, 150
 - IF up-converter mixture, 149
 - Image Rejection Ratio (IRR), 66, 145
 - function of amplitude and phase imbalance, 50, 97
 - Impact on BER performance, 33, 39, 42, 43, 45, 47, 50, 52, 53, 57
 - In-phase / Quadrature (I/Q), 76, 143, 145
 - Input 1-dB compression point, 40, 180
 - Insertion Loss (IL), 199
 - Institute of Electrical and Electronics Engineers (IEEE), 5, 7
 - Integrated Circuit (IC), 22, 25
 - Intermediate Frequency (IF), 135
 - Intermodulation products (IM3), 39, 181
 - International Telecommunication Union (ITU), 15, 236
 - Internet Protocol (IP), 7, 8
 - IRR measurement, 105
 - IRR sensor, 94
- K**
- Keysight E4440A spectrum analyzer, 98
- L**
- Lab synthesizers (HP 83712B and Keysight E8257D), 244
 - Line of Sight (LoS), 3, 28
 - Linearization circuit, 150, 151
 - Link budget
 - atmospheric absorption, 17
 - Boltzmann constant, 18
 - parameters and values for, 19
 - LmCm baseband filter, 56
 - LO feedthrough, 19, 139, 164, 169, 232
 - LO signal power, 37
 - Local Oscillator (LO), 42–44, 64, 142
 - Long-range radar (LRR), 5
 - Long-Term Evolution (LTE), 7, 8
 - LOs in TX-FSYN, 44, 45
 - LOs of the transmitter and receiver analog chain, 25, 30, 43

Lower Side-Band (LSB), 157
 Low-Noise Amplifier (LNA), 20
 Low-Pass Filter (LPF), 242
 LpCp baseband filter, 56

M

Matching Network (MN), 122, 124, 130, 139, 168, 177, 178, 184, 186, 189, 195, 201, 202, 232
 MATLAB program, 98, 101
 Maximum Available Gain (MAG), 186
 Maximum oscillation frequency, 136
 Maxwell equations, 121
 Measuring Device (MD), 71
 Medium Range Radar (MRR), 5
 Metal–insulator–metal (MIM) capacitors, 117
 Metal-Oxide-Metal (MOM), 122, 123, 132, 165, 168, 222
 Metal-Oxide-Semiconductor Field Effect Transistor (MOSFET), 2, 180
 Meyer detector, 217
 Millimeter-Wave (mmW), 1
 MIM capacitors, 122, 123
 MIMO and beamforming technologies, 7
 Minimum Mean Square Error (MMSE), 85
 MmW communication system, 61, 164, 241
 MMW imaging mm
 CMOS and BICMOS technologies, 6
 MmW up-converter, 22, 164, 166, 169, 173
 Modelling DAC delay imbalance, 78
 Modulation Error Ratio (MER), 109, 112
 Monolithic Microwave Integrated Circuit (MMIC), 9, 98, 141
 MOSFET transistors, 117, 165, 178
 M-QAM modulation schemes, 21
 Multiple-Input Multiple-Output (MIMO), 7

N

Near-Field Communication (NFC), 1
 N-MOS transistors, 149, 218, 222
 Noise Figure (NF), 140
 Non-frequency-selective I/Q imbalance, 68, 111
 Non-Frequency-Selective (NFS), 55

O

On-wafer performance, 155
 Output bandwidth, 92, 94, 139, 157, 165, 216, 218, 228
 Output buffer, 44, 222, 227, 229

Output 1-dB compression point (OP 1-dB), 238
 Output transformer, 198, 200

P

Peak to Average Power Ratio (PAPR), 21, 38, 39, 42, 244
 Personal Area Network (PAN), 4
 Phase-Locked Loop (PLL), 43
 Phase Modulation (PM), 181, 193, 194
 Phase noise, 27, 28, 42–45
 Picoprobe, 203
 PolyPhase Filters (PPF), 146
 Post-Layout Simulation (PLS), 164, 169, 171–173
 Pout–pin and gain–pin curves, 205
 Power-Added Efficiency (PAE), 179, 192, 205
 Power Amplifier (PA), 20
 Power combining techniques, 190
 Power Spectrum Analyzer (PSA), 97–101, 105, 107, 109, 112
 Power Spectrum Density (PSD), 28
 Printed Circuit Board (PCB), 155, 160, 162, 223, 235, 241
 Process Design Kit (PDK), 119, 123, 124
 Process, Voltage and Temperature (PVT), 197, 213
 Proportional To Absolute Temperature (PTAT), 198
 Prototype Controller (PrC), 98, 99, 101
 PSA Pre-dist. tones, 105
 PSA- based I/Q imbalance compensation, 97, 98

Q

Quadrature Amplitude Modulation (QAM), 30, 33, 37, 38, 40, 44, 46, 58, 109, 232
 Quadrature LO generation, 154
 Quadrature modulation, 143, 144
 Quadrature Phase-Shift Keying (QPSK), 33, 144, 193, 242

R

Radio Access Network (RAN), 8
 Radio-Frequency Identification (RFID), 1
 Radio Frequency (RF), 1, 19, 20, 25, 28, 39, 58, 59, 69, 90, 121, 122, 135, 137–142, 155, 162, 165, 177–179, 188, 203, 213–217, 222, 223, 235, 241

- Random-Access Memory (RAM), 122
- RC network, 200–202, 216, 218, 221, 229
- Receiver baseband controller, 28, 30
- Receiver I/Q imbalance analysis, 52
- Receiver (RX), 25
- Reed–Solomon (RS), 29
- Remaining I/Q imbalance compensation, 104, 107, 109
- Remaining I/Q imbalance estimation, 95
- Remote Radio Head (RRH), 7
- Resolution Bandwidth (RBW), 245
- RF impairments, 25, 28, 58
- Root-Raised-Cosine (RRC), 16, 21, 242

- S**
- Saturation power (P_{sat}), 180, 238
- Short-Range Radar (SRR), 5
- SiGe BiCMOS process, 2, 117, 147, 195
- Signal-Ground-Signal (SGS), 155
- Signal-to-Noise Ratio (SNR), 18, 19, 28–30, 45, 50, 52, 58, 139
- Silicon-based technologies, 2, 9
- Silicon on Insulator (SOI), 2
- Simulated stability factors of the power amplifier, 201
- Simulation model
 - BER COMP, 26
 - Block BIT sources, 25
 - Block TX-DBB, 26
 - for the I/Q imbalance effect, 46
 - for the nonlinearity effect, 40
 - I/Q symbols, 26
- Single Side-Band (SSB) tone, 145
- SNR curves, 19
- SNR degradation, 52, 139
- SNR of the I/Q symbols, 29
- Spectral mask
 - E-band point-to-point communication links, 16
- Spectrum Analyzer (SA), 71, 112
- Stability, 126, 182, 186, 188, 195, 198–202, 232, 235
- STMicroelectronics, 117, 147, 164, 195, 218, 231
- Sub-Miniature version A (SMA), 160, 241
- Surface-Mount Technology (SMT), 160
- Symmetric and the asymmetric models, 67

- T**
- The noise factor (F), 139

- The Wilkinson combiner, 190
- Third-order Intercept Point (IP3), 181
- Transceiver architecture
 - E-band transceiver, 19
 - Superheterodyne transceiver, 19, 231
- Transistor cell implementation, 131
- Transistor placement and connections in a PA stage, 132
- Transmission Line (TL), 3, 117, 119, 124, 125, 131, 132, 145, 146, 165, 190, 195, 202, 214, 232, 241
- Transmitter design, 231
- Transmitter Digital Baseband processor (TX-DBB), 26, 77, 90, 92, 98, 100, 107
- Transmitter frequency-selective I/Q imbalance, 61, 62, 67, 68, 78, 90, 111
- Transmitter I/Q imbalance analysis, 47, 59, 67
- Transmitter part that comprises baseband and IF (TxBB2IF), 61, 62, 65, 69–74, 78, 90–92
- Transmitter requirements, 21
- Transmitter (TX), 64, 66, 68, 89, 92, 94
- TX-FSYN, 27, 44, 45
- TX-MMW, 27, 39

- U**
- Ultra-Wideband (UWB), 58, 76, 81, 82, 92, 112
- Upper Side-Band (USB), 157–159
- UWB transmitters, 90, 111, 112

- V**
- Variable-Gain Amplifier (VGA), 20
- Vector Network Analyzer (VNA), 236
- Very-Large-Scale Integration (VLSI), 122, 124, 131
- Voltage Controlled Oscillator (VCO), 43

- W**
- Waveguide (WG), 241
- Wideband Code Division Multiple Access (WCDMA), 8
- Wideband millimeter-wave signals
 - effect of front-end imperfections TX-AIF, 26